# PROCESS CPD41

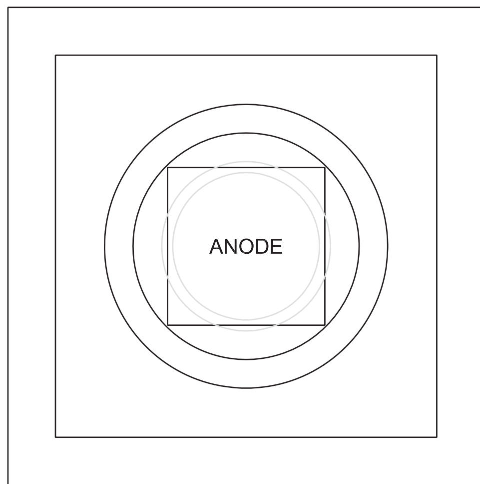
## Switching Diode

### High Current Switching Diode Chip

**PROCESS DETAILS**

| Process | EPITAXIAL PLANAR |
|---|---|
| Die Size | 19.7 x 19.7 MILS |
| Die Thickness | 8.0 MILS |
| Anode Bonding Pad Area | 6.5 x 6.5 MILS |
| Top Side Metalization | Al - 30,000Å |
| Back Side Metalization | Au - 12,000Å |

**GEOMETRY**




BACKSIDE CATHODE R1

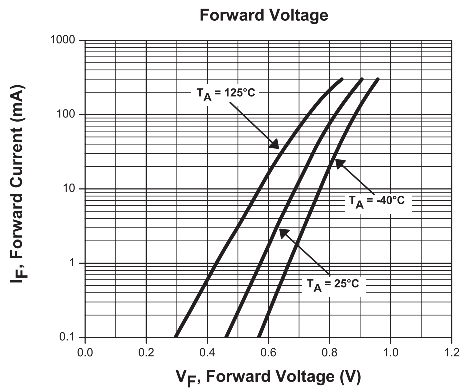
**GROSS DIE PER 4 INCH WAFER**
30,394

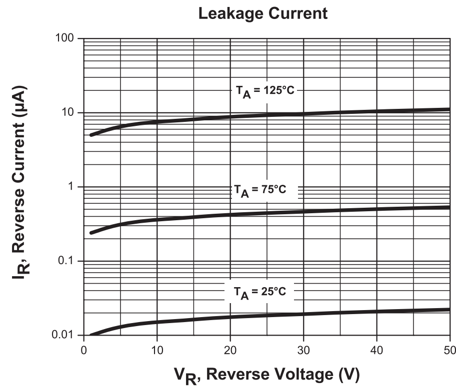
**PRINCIPAL DEVICE TYPES**
1N3600
1N4150
CMPD4150

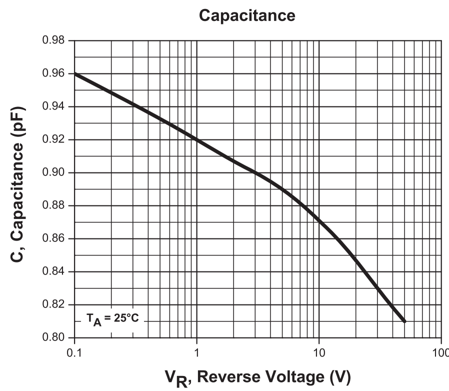
R4 (22-March 2010)

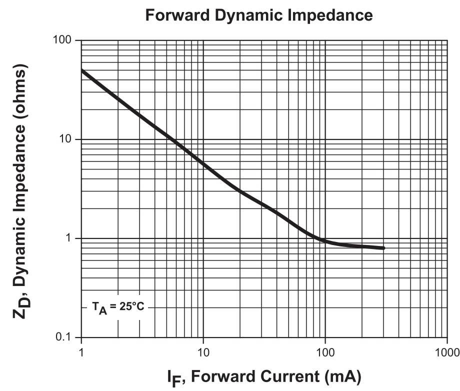
# PROCESS CPD41

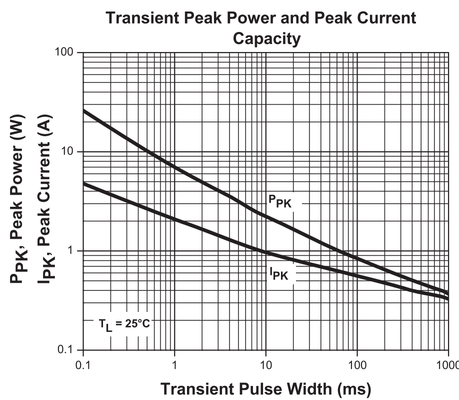
## Typical Electrical Characteristics

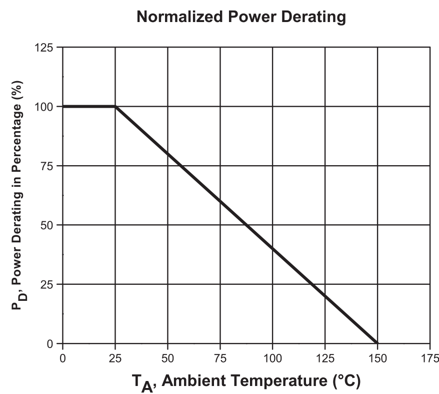



R4 (22-March 2010)